(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
25 September 2008 (25.09.2008)

PCT

(10) International Publication Number
WO 2008/114099 A1

(51) International Patent Classification:
H01L 21/762 (2006.01)

(21) International Application Number:
PCT/IB2007/051435

(22) International Filing Date: 19 March 2007 (19.03.2007)

(25) Filing Language: English

(26) Publication Language: English

(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, Chemin des Franques, F-38190 Bernin (FR).

(72) Inventor; and

(75) Inventor/Applicant *(for US only)*: **KONONCHUK, Oleg** [US/FR]; 4 Place Bir Hakeim, F-38000 Grenoble (FR).

(74) Agents: **COLLIN, Jérôme** et al.; Cabinet Regimbeau, 20, rue de Chazelles, F-75847 Paris Cedex 17 (FR).

(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:
— *of inventorship (Rule 4.17(iv))*

Published:
— *with international search report*

(54) Title: PATTERNED THIN SOI

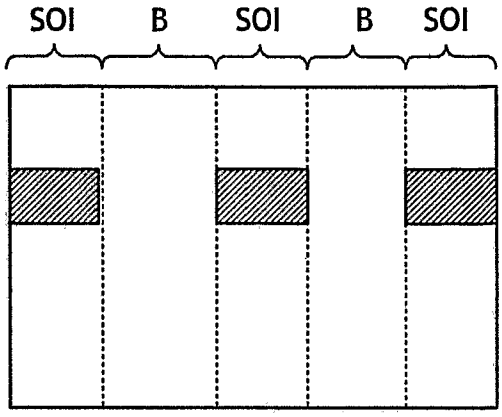


FIG.1

(57) Abstract: The invention relates to a process of treating a structure for electronics or optoelectronics, the structure comprising successively: - a bulk substrate, - an oxide layer, and - a semiconductor layer. The process comprises providing masking means to define on the semiconductor layer a desired pattern, and applying a thermal treatment for removing a controlled thickness of oxide in the regions of the oxide layer corresponding to said desired pattern.

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